

appropriate fee under 37 C.F.R. §§ 1.16 to 1.21 from Williams, Morgan & Amerson, P.C. Deposit Account No. 50-0786/2008.002800. Reconsideration of the application in view of the following amendments and remarks is respectfully requested.

AMENDMENT

Please amend claim 31 and add new claims 48-54 as follows.

- A1
31. (Amended) A phosphor particle bounded substrate, comprising:
- a substrate having first and second surfaces;
 - an anode electrode formed on the first surface of the substrate;
 - a fluorescent material layer (FML) formed on the anode electrode, the FML having phosphor particles disposed therein;
- wherein the phosphor particles are bound to the substrate by submerging the substrate into a binder solution and removing the substrate from the binder solution at a predetermined rate.
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- A2
48. (New) A substrate, comprising:
- an anode electrode formed on a first surface of the substrate; and
 - a fluorescent material layer (FML) formed on the anode electrode, the FML having phosphor particles that are bound to the anode electrode by removing the substrate from a binder solution at a predetermined rate.

49. (New) The substrate of claim 48, wherein the binder solution comprises a solution of approximately 0.1%-2.0 % by body weight potassium silicate in water.

50. (New) The substrate of claim 48, wherein the binder solution comprises water and at least one of potassium silicate, sodium silicate, ammonium silicate and polyvinyl alcohol.

51. (New) The substrate of claim 48, wherein the binder solution comprises alcohol and organo-silicate.

52. (New) The substrate of claim 48, wherein the predetermined rate is approximately one inch per minute.

53. (New) The substrate of claim 48, wherein the phosphor particles are bound to the substrate by submerging the substrate into a binder solution, removing the substrate from the binder solution at a predetermined rate, and placing the substrate into a furnace to heat the substrate to a temperature between about 400° and 700° C.

54. (New) The substrate of claim 53, wherein the substrate is heated to a temperature between about 400° and 500° C.

REMARKS

Claims 1-47 remain pending in the present application. Claims 1-15 and claims 38-47 were withdrawn from consideration by the Examiner in accordance with 37 CFR 1.142(b) as being drawn to a non-elected invention in a previous restriction requirement. New claims 48-54